Quantum dots in photonic crystal cavities

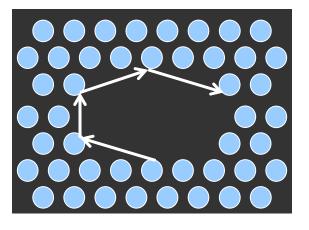
Stephanie Manz, 18-06-2009

Seminar Elements of Nanophotonics

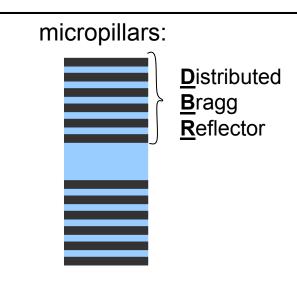
- cQED: interaction between single emitter and cavity
- solid state cavity + quantum dot: small mode volume
- \rightarrow strong coupling regime (g₀ ~ V^{-1/2})

cavities: photonic crystals and micropillars

photonic crystal cavities:



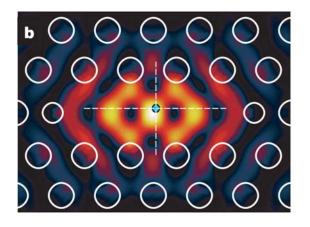
- band gap material
- membrane can consist of layers
- total internal reflection in plane
- cavity modes according to geometry
- typical scale: 200 500 nm



- DBR act as mirrors
- radial confinement by tot. int. Ref
- typical scale: 1µm x n*500nm

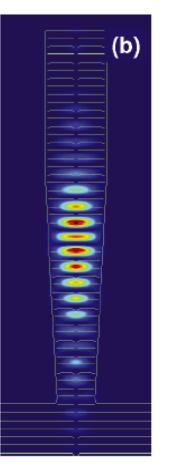
cavities: photonic crystals and micropillars

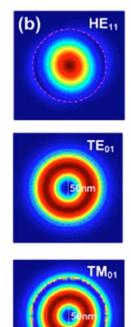
photonic crystals:



 quantum dot placed in maximum of cavity mode (might be off center)

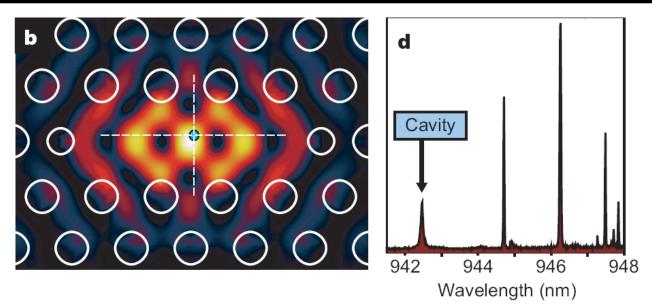
micropillars:





lecture notes; Yinan, Opt. Lett. ,34 ,7 (2009)

quantum dot – cavity coupling

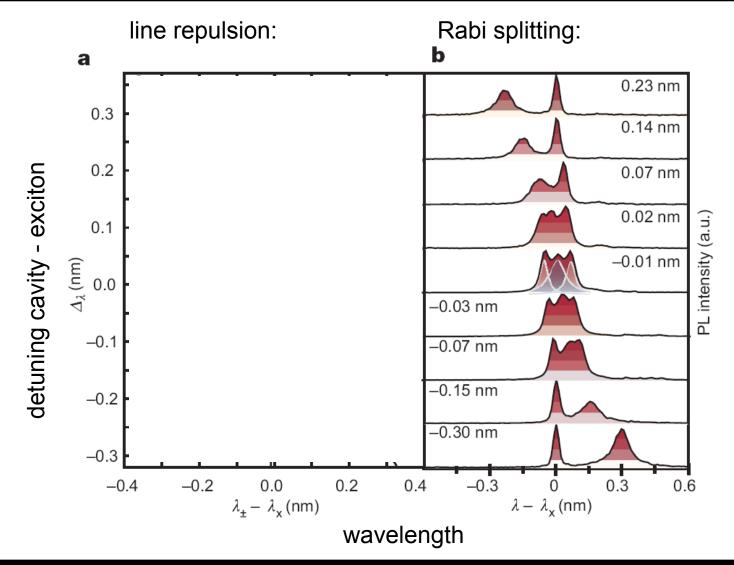


- quantum dot is prepared on substrate (random position)

- cavity is fabricated arround, overlap mode with QD
 → quantum dot emissions, cleary separated
- tune cavity mode further
- proove existence of single emitter by $g^{(2)}(t=0)$ measurment

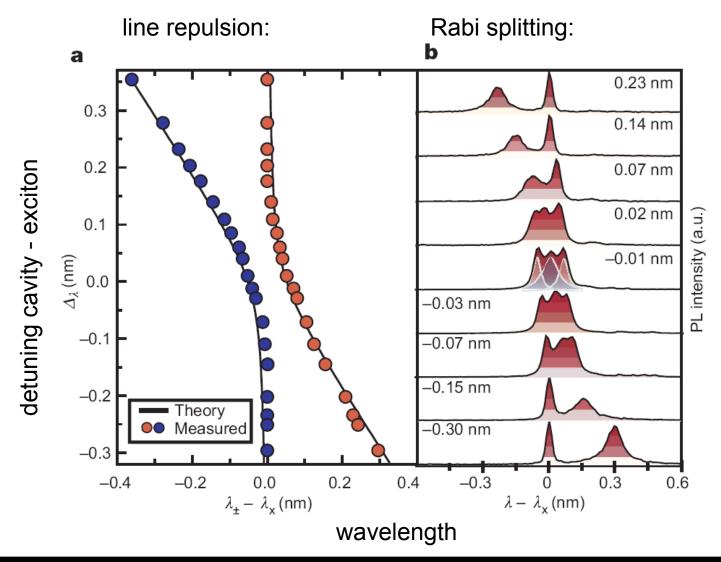
Quantum nature of a strongly coupled single quantum dot–cavity system K. Hennessy, ..., A. Imamoglu, nature 05586, 1 (2007)

strong coupling: line repulsion and Rabi splitting



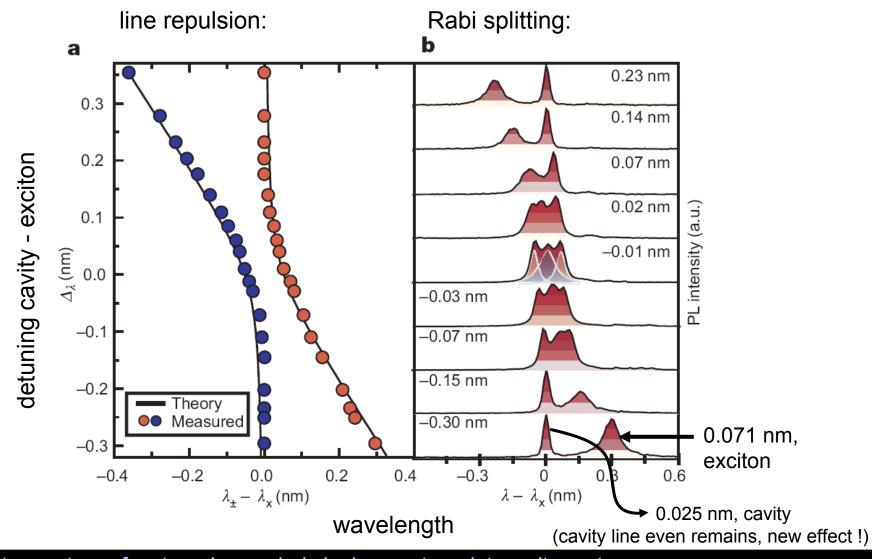
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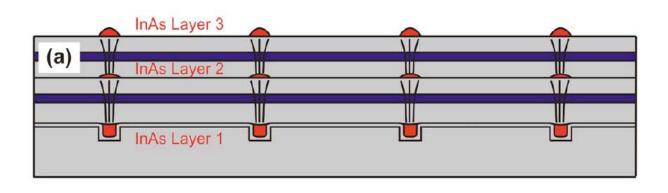
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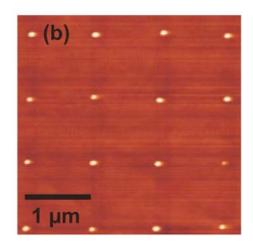
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site control in micropillar

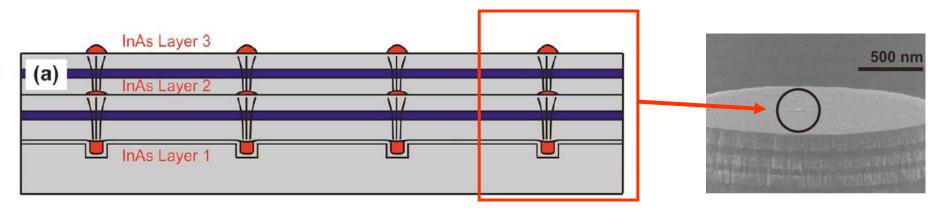




fabrication:

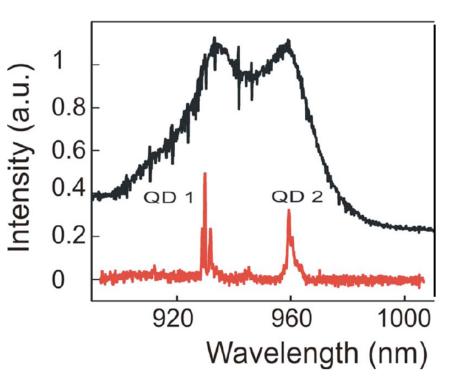
- bottom part of DBR (AIAs / GaAs)
 - bottom half of cavity (GaAs)
 - lithography / etching of nano-holes
 - overgroth
 - grow quantum dot, repeat three times to improve quality
- \rightarrow quantum dots form at former hole position
- \rightarrow strain remains after overgroth \rightarrow quantum dots stacked

site control in micropillar



- fabrication: bottom part of DBR (AIAs / GaAs)
 - bottom half of cavity (GaAs)
 - lithography / etching of nano-holes
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characterization



black:

quantum dot emission <u>without cavity</u> (top DBR layer has been removed)

ightarrow 2 peaks according to second / third layer

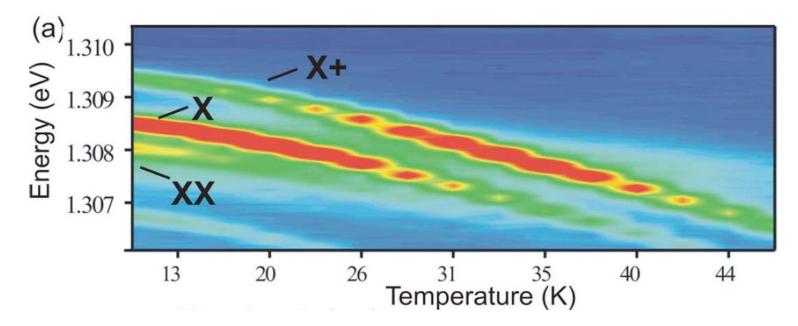
red:

QD emission inside cavity:

 \rightarrow lines from different QD separated

spectrum can be resolved

spectroscopy and tuning

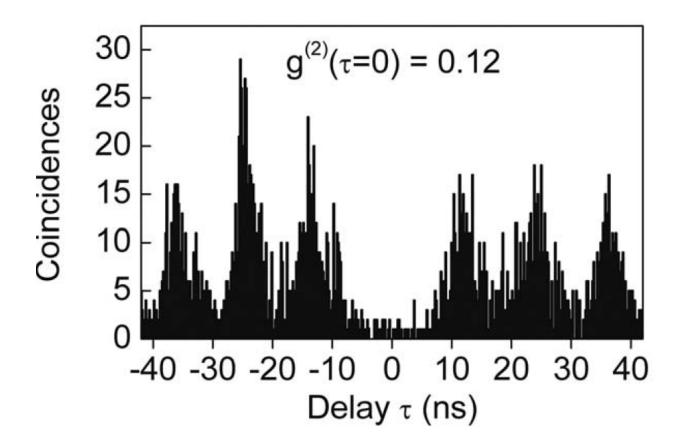


substructure of quantum dot spectrum:

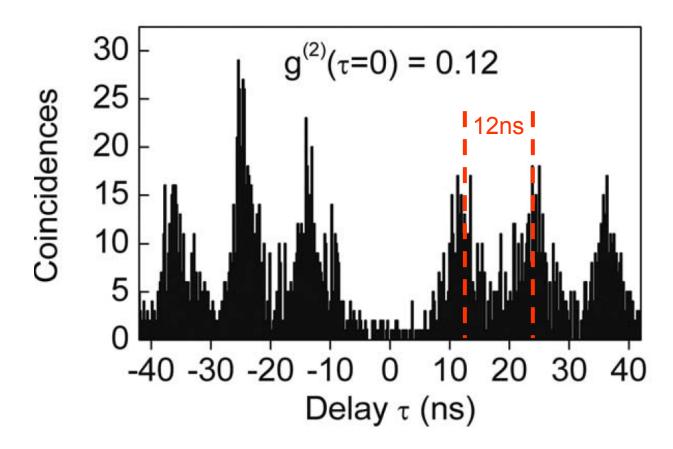
- X: excitonic emission (electron-hole pair)
- X+: positively charged emission (trion / charged electron-hole pair)
- XX: biexcitonic emission ("bound" electron-hole pairs)

cavity can be tuned in resonance with each line by temperature control

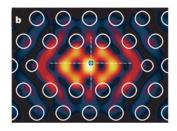
cavity tuned to the X+ transition:



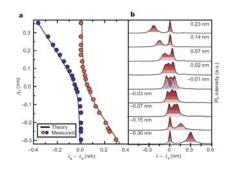
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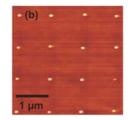
summary



couple quantum dots to cavity modes



strong coupling regime possible



position control of quantum dots

Stephanie Manz